CERTIFICATE OF TRANSLATION

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TRANSISTOR

and believe that the translation is true and correct.

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Shigeo Ishijima

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【Scope of Invention】

【Claim 1】 A transistor comprising:

a semiconductor substrate having a drain layer of a first conductivity type, and an oppositely conductive region of a second conductivity type provided on said drain layer and different from said first conductivity type;

a trench formed such that it extends from said oppositely conductive region of said semiconductor substrate to said drain layer;

a source region of the first conductivity type formed in said oppositely conductive region and exposed on an inner circumferential surface of said trench;

a gate insulating film formed on the inner circumferential surface of said trench and provided such that it reaches to said drain layer, said oppositely conductive region and said source region;

a gate electrode film provided in tight contact with said gate insulating film;

a source electrode film provided such that it is insulated from said gate electrode film and in contact with at least said source region exposed on the inner circumferential surface of said trench.

【Claim 2】 A transistor according to Claim 1, further comprising an insulating film thicker than said gate insulating film provided between said gate electrode film in said trench and said source electrode film.

【Detail description of the invention】

【0001】

【Technical Field of Invention】

The present invention relates to transistors and, more particularly, to power MOSFETs which are used in most power supply circuits and the like.

【0002】

【Prior Art】

Reference number 101 in Figs. 17(a) and (b) represents a trench type power MOSFET according to the related art. Fig. 17(b) is a sectional view taken along the line C-C in Fig. 17(a).

【0003】

As shown in Fig. 17(b), the power MOSFET 101 has a semiconductor substrate 105 provided by forming a drain layer 112 constituted by an N^--type epitaxial layer and P-type body regions 115 on an N^+-type silicon substrate 111 sequentially. The power MOSFET 101 also has a plurality of cells 103 as shown in fig. 17(b). The plurality of rectangular cells 103 is formed in a staggered configuration on a top surface of the semiconductor substrate 105. Fig. 17(a) shows six cells 103_1 through 103_6 and omits a source electrode film which will be

described later.

【0004】

As shown in Fig. 17(b), a trench 118 having a rectangular section whose bottom extends into the drain layer 112 is formed in the P-type body region 115 of each cell 103, and a P^+-type diffusion region 124 extending to a predetermined depth from the top surface of the P-type body region 115 is formed in a position between adjacent trenches 118. An N^+-type source region 127 extending to a depth short of the drain layer 112 from the surface of the P-type body region 115 is formed around the P+-type diffusion region 124 and around the opening of the trench.

【0005】

A gate insulating film 119 is formed on the inner circumferential surface and the bottom surface of the trench 118, and a polysilicon gate 130 is formed on the surface of the gate insulating film 119 such that it fills the interior of the trench 118 and such that the upper end thereof is located higher than the lower end of the source region 127.

【0006】

A PSG (phosphosilicate glass) film 128 is formed on top of the polysilicon gate 130, and a source electrode film 129 made of Al is formed to coat the top surfaces of the PSG film 128 and the semiconductor substrate 105. The polysilicon gate 130 and source electrode film 129 are electrically insulated

by the PSG film 128.

【0007】

In a power MOSFET 101 having such a structure, when a voltage equal to or higher than a threshold voltage is applied across the polysilicon gates 130 and the source electrode film 129 with a high voltage applied across the source electrode film 129 and drain layer 112, inversion layers are formed at interfaces between the gate oxide films 119 and P-type body regions, and a current flows from the drain to the source through the inversion layers.

【0008】

In a power MOSFET 101 having the above-described structure, the PSG films 128 must be patterned using photolithography to provide direct contact between the source electrode film 129 and each of the source regions 127 on the top surfaces of the source regions 127. Since misalignment of the PSG films 128 can occur when they are formed using such a method, the area occupied by the PSG films 128 on the top surface of the semiconductor substrate 105 includes some margin to ensure insulation between the source electrode film 129 and polysilicon gates 130 even if there is some misalignment.

Consequently, the PSG films 128 are formed not only above the trench 118 but also around the openings of the trench.

【0009】

Therefore, the parts of the source regions 127 formed

around the openings of the trench 118 are therefore located under the PSG films 128 and, in order to provide contact between the source electrode film 129 and the source regions 127 with a sufficiently low resistance, a large area of the source regions 127 must be exposed in advance on the top surface of the semiconductor substrate. As a result, the area occupied by the source regions 127 on the top surface of the semiconductor substrate 105 can not be reduced beyond a certain limit, and this has hindered efforts toward finer devices.

【0010】

【Problem to be solve by the invention】

The present invention has been conceived to solve the above-described problems with the related art, and it is an object of the invention to provide a technique which makes it possible to reduce the area occupied by cells to be formed on a substrate, thereby allowing a reduction of the size of devices.

【0011】

【Means to solve the problem】

In order to solve the above-described problems, according to a first aspect of the invention, there is provided a transistor having:

a semiconductor substrate having a drain layer of a first conductivity type, and an oppositely conductive region of a second conductivity type provided on said drain layer and

different from said first conductivity type;

a trench formed such that it extends from said oppositely conductive region of said semiconductor substrate to said drain layer;

a source region of the first conductivity type formed in said oppositely conductive region and exposed on an inner circumferential surface of said trench;

a gate insulating film formed on the inner circumferential surface of said trench and provided such that it reaches to said drain layer, said oppositely conductive region and said source region;

a gate electrode film provided in tight contact with said gate insulating film;

a source electrode film provided such that it is insulated from said gate electrode film and in contact with at least said source region exposed on the inner circumferential surface of said trench.

According to a second aspect of the invention, there is provided a transistor having an insulating film thicker than said gate insulating film provided between said gate electrode film in said trench and said source electrode film.

layer.

【0012】

A transistor according to the related art has a structure in which a source region is exposed on a top surface of a

semiconductor substrate and is in direct contact with a source electrode at the exposed surface. It has been therefore necessary to allow the source region to occupy a somewhat large area on the top surface of the substrate to provide a large contact area between the source electrode and source region in order to maintain a predetermined conduction resistance.

【0013】

On the contrary, in a transistor according to the invention, since a source electrode film is in direct contact with a source region at least in a part of the source region exposed on an inner circumferential surface of a trench, the contact area between the source region and source electrode film can be made substantially as large as that in the related art by exposing a large area of the source region on the inner circumferential surface of the trench even if the area occupied by the source region on the top surface of the semiconductor substrate is smaller than that in the related art.

【0014】

This makes it possible to provide source contact between the source region and source electrode film with a sufficiently low resistance as in the related art and to reduce the size of the device by reducing the area occupied by the source region on the top surface of the semiconductor substrate compared to that in the related art.

【0015】

【Working of the invention】

A preferred embodiment of the present invention will now be described with reference to the drawings.

Reference number 1 in Figs. 1(a) and (b) represents a trench type power MOSFET according to an embodiment of the invention. Fig. 1(b) is a sectional view taken along the line A-A in Fig. 1(a).

【0016】

As shown in Fig. 1(b), the power MOSFET 1 has a semiconductor substrate 5 provided by forming a drain layer 12 constituted by an N^--type epitaxial layer and P-type body regions 15 on an N^+-type silicon substrate 11 sequentially. As shown in Fig. 1(a), a plurality of cells 3 are formed in the form of a grid on a top surface of the semiconductor substrate 5. Fig. 1(a) shows six cells 3_1 through 3_6 and omits a source electrode film which will be described later.

【0017】

As shown in Fig. 1(b), a trench 18 whose bottom extends into the drain layer 12 is formed in the P-type body region 15 of each cell 3, and a P^+-type diffusion region 24 extending to a depth short of the drain layer 12 from the top surface of the P-type body region 15 is formed in a position between adjacent trenches 18. An N^+-type source region 27 extending to a depth short of the drain layer 12 from the top surface of the P-type body region 15 is formed around the P^+-type diffusion region

24 and around the trench 18.

【0018】

The trench 18 is filled with polysilicon gates 30, and the upper ends of the polysilicon gates 30 are located above the lower end of the source regions 27. Gate insulating films 19 are formed between the polysilicon gates 30 and the inner circumferential surface and bottom surface of the trench 18.

【0019】

In a power MOSFET 1 having such a structure, when a voltage equal to or higher than a threshold voltage is applied across the polysilicon gates 30 and source regions 27 with a high voltage applied across the source electrode film 29 and drain layer 12, inversion layers are formed at interfaces between the gate insulating films 19 and P-type body regions 15, and a current flows from the drain to the source through the inversion layers.

【0020】

In the present embodiment, the N-type corresponds to the first conductivity type, and the P-type corresponds to the second conductivity type. The P-type body region 15 and P^+-type diffusion region 24 forms an example of the oppositely conductive region according to the present invention.

【0021】

A description will now be made with reference to Figs. 2(a) through 8(u) on steps for forming individual cells 3_1

through 3_6 on a silicon substrate 11. Fig. 8(u) is a sectional view taken along the line B-B in Fig. 1.

【0022】

First, a drain layer 12 constituted by an N^--type epitaxial layer having a thickness in the range from 4 to 5 μm and resistivity of 0.3 Ω·cm is formed on a top surface of an N^+-type silicon substrate 11 having resistivity of 3×10^{-3} Ω·cm (Fig. 2(a)).

【0023】

Next, a thermal oxidation process is performed to form a SiO_2 film 13 on the entire surface of the drain layer 12 (Fig. 2(b)). When boron ions (B^+) are implanted in the drain layer 12 through the SiO_2 film 13, a p^+-type implantation layer 14 is formed in the drain layer 12 in the vicinity of a top surface thereof (Fig. 2(c)).

Next, a thermal process is performed to diffuse the p^+-type implantation layer 14 in the drain layer 12, thereby forming a P-type body region 15 extending to a depth of 2 μm from the top surface of the drain layer 12 (Fig. 3(d)).

【0024】

Next, the CVD method is performed to form a thick SiO_2 film 16 on the SiO_2 film 13 (Fig. 3(e)), a patterned resist film (not shown) is formed on a top surface of the SiO_2 film 16, and the SiO_2 films 16 and 13 are thereafter etched and removed using the resist film as a mask. Then, an opening 17 is formed through

the SiO_2 films 16 and 13, and a part of the top surface of the P-type body region 15 is exposed on the bottom of the opening 17 (Fig. 3(f)).

【0025】

Next, the resist film is removed, and anisotropic etching such as reactive ion etching is carried out using the SiO_2 films 16 and 13 formed with the opening 17 as a mask. As a result, the P-type body region 15 is etched, and a trench 18 having a width of about 0.6 μm and a rectangular section and extending through the P-type body region 15 to reach the drain layer 12 is formed in the P-type body region 15 in the location where the opening 17 has been formed (Fig. 4(g)). The depth of the trench 18 is greater than the thickness of the P-type body region 15, and the bottom surface thereof is located below the upper end of the drain layer 12.

【0026】

Silicon is exposed in the trench 18 in this state, and a thermal oxidation process is performed after removing the SiO_2 films 16 and 13 (Fig. 4(h)) to expose the top surface of the P-type body region 15 to form a gate insulating film 19 constituted by a silicon oxide film on the entire surface thereof (Fig. 4(i)). In this invention, the gate insulating film 19 is formed with a thickness of 500 Å.

【0027】

Next, the CVD method is performed to form a polysilicon

thin film doped with phosphorous on the gate insulating film 19, and the interior of the trench 18 is then filled with a polysilicon thin film 20 thus formed (Fig. 5(j)).

Next, the polysilicon thin film 20 is etched for a predetermined period of time to remove the polysilicon thin film 20 on the semiconductor substrate with the polysilicon thin film 20 left in the trench 18. At this time, etching is not terminated when the polysilicon thin film 20 on the top surface of the semiconductor substrate is completely removed in order to etch also the top surface of the polysilicon thin film 20 left in the trench 18. Hereinafter, the polysilicon layer left in the trench 18 is referred to as "polysilicon gate" and indicated by reference number 30 (Fig. 5(k)). The polysilicon gate 30 is formed in contact with the gate insulating film 19, and the lower end of the same is located below the top surface of the drain layer 12.

【0028】

In this state, the gate insulating film 19 is exposed on the top surface of the semiconductor substrate and at an upper part of the trench 18 and when the gate insulating film 19 is etched, the top surface of the semiconductor substrate and the inner circumferential surface of the upper part of the trench 18 are exposed (Fig. 5(l)).

【0029】

Next, a thermal oxidation process is performed to oxidize

the part of the semiconductor substrate where silicon is exposed and the polysilicon gate 30 exposed in the trench 18 to form a cap oxide film 21 on the entire surface of such regions (Fig. 6(m)).

【0030】

Next, a patterned resist film 22 is formed on the top surface of the semiconductor substrate, and boron ions are implanted with the upper part of the trench 18 covered with the resist film 22, which forms P-type implantation layers 23 on the top surfaces of the P-type body regions 15 (Fig. 6(n)).

【0031】

Next, the resist film 22 is removed, and a thermal process is performed to diffuse the P^+-type implantation layers 23 in the P-type body regions 15, thereby forming P^+-type diffusion regions 24 to a depth of about 1 μm from the top surfaces of the P-type body regions 15 (Fig. 6(o)).

【0032】

Next, a resist film 25 having an opening in a region corresponding to the trench 18 and the neighborhood thereof is formed on the cap oxide film 21 (Fig. 7(p)). Phosphorous ions (P^+) are implanted through the opening of the resist film 25 using the resist film 25 as a mask, and the phosphorous ions (P^+) are then implanted in the P-type body regions 15 to form N^+-type implantation layers 26 in the vicinity of the top surfaces of the P-type body regions 15 (Fig. 7(q)).

【0033】

Thereafter, a thermal process is performed to diffuse the N^+-type implantation layers 26 to form source regions 27 constituted by N^+-type impurity diffusion layers that extend from the top surfaces of the P-type body regions 15 around the trench 18 in the direction of the depth thereof. The lower ends of the source regions 27 in the parts thereof in contact with the inner circumferential surface of the trench 18 are located below the upper end of the gate insulating film 19 and the upper end of the polysilicon gate 30.

【0034】

That is, the upper ends of the gate insulating film 19 and polysilicon gate 30 are located above the lower ends of the source regions 27 on the side thereof closer to the inner circumferential surface of the trench 18 and, as described above, the lower ends of them are located below the upper end of the drain layer 12.

【0035】

Therefore, the gate insulating film 19 and polysilicon gate 30 are provided such that they reach to the drain layer 12, P-type body regions 15 and source regions 27 on the inner circumferential surface of the trench 18 as shown in Fig. 7(r).

【0036】

Next, the CVD method is performed to form an insulating film 28 constituted by a PSG film on the cap oxide film 21 such

that it extends on the top surface of the substrate and in the interior of the trench 18 (Fig. 8(s)).

Next, the insulating film 28 and cap oxide film 21 are etched for a predetermined period of time to remove the insulating film 28 and cap oxide film 21 on the P-type body regions 15 and to remove the insulating film 28 and cap oxide film 21 formed in the vicinity of the opening of the trench 18, which exposes the top surface of the semiconductor substrate and the inner circumferential surface of the upper part of the trench 18 (Fig. 8(t)).

Thereafter, an Al thin film is formed on the entire surface using evaporation to form a source electrode film 29 (Fig. 8(u)). The cells 3 are formed through the above-described steps.

【0037】

In the power MOSFET 1 of the present embodiment as described above, the source electrode film 29 and source region 27 in each cell 3 are in direct contact with each other on a top surface 51 of the semiconductor substrate 5 and on an inner circumferential surface 52 of the trench 18, and are electrically connected to each other.

【0038】

Therefore, even when the source regions 27 are formed in a small area on the semiconductor substrate 5, the contact area between the source regions 27 and source electrode film

29 can be increased by increasing the area of the source regions 27 exposed on the inner circumferential surface 52 of the trench 18.

【0039】

Since there is no need for increasing the area occupied by each source region 27 to maintain source contact with a sufficiently low resistance as in the related art, the area occupied by the source regions 27 can be smaller than that in the related art, and this makes it possible to reduce the size of devices.

【0040】

While the width Δw of the source regions 27 on the top surface of the semiconductor substrate 5 can be reduced only to about 1 μm in a structure according to the related art, the inventors of the present invention have confirmed that the structure of the present embodiment makes it possible to reduce the width Δw of the source regions 27 to 0.5 μm or less.

【0041】

Thus, in the power MOSFET 1 of the present embodiment, the width Δw of the source region 27 of one cell can be reduced by 50 % or more, and the area occupied by the same can therefore be also reduced significantly.

【0042】

For example, when the width of a P^+-type diffusion region 24 was set at 1 μm and the width Δw of a source region according

to the related art was set at 1.3 μm, the area occupied by the source region in the structure according to the related art was $(1 + 1.3 \times 2)^2 - 1^2 = 11.96$ (μm^2). On the contrary, when the width of a P^+-type diffusion region 24 according to the present invention is set at 1 μm as in the related art and the width Δw of a source region is set at 0.5 μm, the area occupied by the source region in the structure according to the invention is $(1 + 0.5 \times 2)^2 - 1^2 = 3$ (μm^2). In this case, the area can be reduced by 75 % in terms of the area ratio. Therefore, a significant reduction of the area for the formation of this region can be achieved in a power MOSFET as a whole.

【0043】

It is therefore possible to obtain cells 3 in which contact between a source electrode film 29 and source regions 27 is provided on an inner circumferential surface 52 of a trench 18 as described above, and such cells can be also manufactured through steps as described below.

【0044】

First, a polysilicon gate 30 is formed in a trench 18 at the steps described with reference to Figs. 2(a) through 5(k). The step in Fig. 5(k) is followed by photolithography to form a resist film 31 which covers the trench 18 from above and covers the neighborhood of the trench 18 (Fig. 10(l)), and boron ions (B^+) are implanted into P-type body regions 15 using the same as a mask to form P^+-type implantation layers 23 on top surfaces

of the P-type body regions 15 (Fig. 10(m)).

【0045】

Next, the resist film 31 is removed, and a thermal process is performed to thermally diffuse the P^+-type implantation layers 23 in the P-type body regions 15, thereby forming P^+-type diffusion regions 24 to a depth short of a drain region 12 from the top surfaces of the P-type body regions 15 (Fig. 10(n)).

【0046】

Next, a patterned resist film 34 is formed on a gate insulating film 19 (Fig. 11(o)). Phosphorous ions (P^+) are implanted in the P-type body regions 15 with regions excluding the trench 18 and the neighborhood thereof covered by the resist film 34 through the gate insulating film 19 to form N^+-type implantation layers 26 in the vicinity of the top surfaces of the P-type body regions 15 (Fig. 11(p)).

【0047】

Next, the resist film 34 is removed, and a thermal process is performed to diffuse the N^+-type implantation layers 26 in the P-type body regions 15 to form source regions 27 constituted by N^+-type impurity diffusion layers that extend from the top surfaces of the P-type body regions 15 around the trench 18 in the direction of the depth thereof. The lower ends of the source regions 27 in the parts thereof on the side of the inner circumferential surface of the trench 18 are located below the upper end of the polysilicon gate 30 (Fig. 11(q)).

【0048】

In this state, the gate insulating film 19 is exposed on the top surface of the semiconductor substrate and at an upper part of the trench 18 and when the gate insulating film 19 is etched and removed, the top surface of the semiconductor substrate and the inner circumferential surface of the upper part of the trench 18 are exposed (Fig. 12(r)).

【0049】

Next, the CVD method is performed to form an insulating film 28 constituted by a PSG film on the top surface of the polysilicon gate 30 exposed in the trench 18, the inner circumferential surface of the trench 18 and the top surfaces of the P-type body regions 15, thereby filling the trench 18 with the insulating film 28 (Fig. 12(s)).

【0050】

Next, the insulating film 28 is etched for a predetermined period of time to remove the insulating film 28 on the top surface of the semiconductor substrate and to also etch the top surface of the insulating film 28 left in the trench 18 (Fig. 12(t)).

Thereafter, an Al thin film is formed on the entire surface using evaporation to form a source electrode film 29 (Fig. 13(u)).

【0051】

In a cell formed in such a manner, the source electrode film 29 is in direct contact with the top surface of the source

region 27 and a lateral surface thereof exposed on the inner circumferential surface of the trench 18, and electrical connection with the source electrode film 29 is established in those parts in contact therewith. Therefore, since a predetermined conduction resistance can be maintained even when the source region 27 occupies a small area on the top surface of the semiconductor substrate 5, the area occupied by the source region 27 can be smaller than that in the related art to allow a smaller device size.

【0052】

Further, such cells in which contact between a source electrode film 29 and source regions 27 is established on an inner circumferential surface 52 of a trench 18 may be used in an IGBT (insulated gate bipolar mode transistor).

【0053】

An IGBT having such a cell structure can be obtained by first providing a P^+-type silicon substrate 61 and by forming an N^--type epitaxial layer 12 having a thickness in the range from 50 to 60 μm and resistivity of 25 Ω·cm on a top surface of the P^+-type silicon substrate 61 (Fig. 14(a)).

【0054】

Thereafter, after performing the steps in Figs. 2(b) through 8(u), a metal film 70 is formed on a bottom surface of the P^+-type silicon substrate 61 to establish ohmic contact with the P^+-type silicon substrate 61, thereby forming an IGBT 4

having the structure shown in Fig. 14(b). In the IGBT 4, a source region 27, P^+-type silicon substrate 61 and polysilicon gate 30 serve as the emitter, collector and gate, respectively.

【0055】

Such a cell structure may be used in a Schottky barrier type IGBT.

A Schottky barrier type IGBT can be obtained by first providing an N^--type silicon substrate 71 (Fig. 15(a)) and by processing a top surface of the N^--type silicon substrate 71 at the steps in Figs. 2(b) through 8(u) to obtain the structure shown in Fig. 15(b). Thereafter, the thickness of the N^--type silicon substrate 71 may be reduced by grinding the bottom side thereof (Fig. 15(c)), and a metal film 80 may be formed on a bottom surface of the substrate 71 to establish Schottky contact with the N^--type silicon substrate 71, thereby providing a Schottky barrier type IGBT 5 having the structure shown in Fig. 15(d). In the Schottky barrier type IGBT 5, a source region 27, N^--type silicon substrate 71 and polysilicon gate 30 serve as the emitter, collector and gate, respectively.

【0056】

An IGBT 6 may be provided in which a P^+-type diffusion region 92 and an N^+-type diffusion region 93 are formed on a bottom surface of an N^--type silicon substrate 71 as in the structure in Fig. 15(b) and in which a bottom surface electrode 94 constituted by a metal film is formed on the entire bottom

surface of the N^--type silicon substrate 71 (Fig. 16(a)).

【0057】

Further, as shown in Fig. 16(b), a structure of a bidirectional conduction switch 7 may be provided in which a transistor P_2 having completely the same configuration as that of a transistor P_1 is formed on a bottom surface of an N^--type silicon substrate 71 formed with the transistor P_1 having the structure shown in Fig. 8(u) on a top surface thereof. In Fig. 16(b), reference numbers 15b, 19b, 24b, 27b, 28b, 29b and 30b correspond to reference numbers 15a, 19a, 24a, 27a, 28a, 29a and 30b respectively and represent like parts.

【0058】

While the above-described embodiment has referred to a power MOSFET 1, an IGBT 4,6, a Schottky barrier type IGBT 5 and a bidirectional conduction switch 7, transistors according to the present invention include all of such devices.

【0059】

The configuration of the cells 3_1 through 3_6 in the above-described embodiment is not limited to grid-like configurations as shown in Fig. 1(a) and, for example, a staggered configuration as shown in Fig. 9 may be employed.

【0060】

In the present embodiment, as described above, the N-type corresponds to the first conductivity type, and the P-type corresponds to the second conductivity type. This is not

limiting the present invention, and the P-type and N-type may correspond to the first and second conductivity types, respectively.

While a PSG film is used as an insulating film 28, the present invention is not limited to such an insulating film and, for example, a silicon nitride film may be used instead.

【0061】

While an Al film is used as a source electrode film 29, the present invention is not limited thereto and, for example, a copper film may be used instead.

While a drain layer 12 is formed as a result of epitaxial growth, a drain layer 12 according to the present invention is not limited to such a method of formation and may be formed using surface diffusion.

【0062】

While cells 3_1 through 3_6 have a rectangular configuration as shown in Fig. 1(a), the present invention is not limited to such a cell configuration and, for example, circular cells may be employed.

In the above-described step for forming cells, source regions 27 are formed on top surfaces of P-type body regions 15 after a trench 18 is formed. However, this is not limiting the present invention, and the trench 18 may be formed after the source regions 27 are formed in advance on the top surfaces of the P-type body regions 15.

【0063】

While all of the semiconductor substrates used in the above-described embodiment are silicon substrates, the present invention is not limited to such semiconductor substrates and may be applied to, for example, a substrate made of SiC or the like.

【0064】

While a polysilicon gate is used as a gate electrode, the present invention is not limited to such a gate electrode and may be applied to a metal gate.

While the above-described embodiment has referred to transistors having a cell structure, the invention is not limited thereto and may be applied to transistors having a stripe configuration.

While a silicon oxide film is used as a gate insulating film 19, a gate insulating film 19 according to the present invention is not limited thereto and, for example, a silicon nitride film or a composite film consisting of a silicon oxide film and a silicon nitride film may be used.

【0065】

【Effects of the invention】

The present invention makes it possible to reduce the area occupied by source regions on the top surface of a semiconductor substrate, thereby allowing a reduction of the size of devices.

【Brief description of the drawings】

Fig. 1(a) is a plan view illustrating a configuration of cells of a power MOSFET according to an embodiment of the invention.

Fig. 1(b) is a sectional view illustrating the power MOSFET according to the embodiment of the invention.

Fig. 2(a) is a sectional view illustrating a step of forming a cell according to the invention.

Fig. 2(b) is a sectional view illustrating a step following the step in Fig. 2(a).

Fig. 2(c) is a sectional view illustrating a step following the step in Fig. 2(b).

Fig. 3(d) is a sectional view illustrating a step following the step in Fig. 2(c).

Fig. 3(e)is a sectional view illustrating a step following the step in Fig. 3(d).

Fig. 3(f) is a sectional view illustrating a step following the step in Fig. 3(e).

Fig. 4(g) is a sectional view illustrating a step following the step in Fig. 3(f).

Fig. 4(h) is a sectional view illustrating a step following the step in Fig. 4(g).

Fig. 4(i) is a sectional view illustrating a step following the step in Fig. 4(h).

Fig. 5(j) is a sectional view illustrating a step

following the step in Fig. 4(i).

Fig. 5(k) is a sectional view illustrating a step following the step in Fig. 5(j).

Fig. 5(l) is a sectional view illustrating a step following the step in Fig. 5(k).

Fig. 6(m) is a sectional view illustrating a step following the step in Fig. 5(l).

Fig. 6(n) is a sectional view illustrating a step following the step in Fig. 6(m).

Fig. 6(o) is a sectional view illustrating a step following the step in Fig. 6(n).

Fig. 7(p) is a sectional view illustrating a step following the step in Fig. 6(o).

Fig. 7(q) is a sectional view illustrating a step following the step in Fig. 7(p).

Fig. 7(r) is a sectional view illustrating a step following the step in Fig. 7(q).

Fig. 8(s) is a sectional view illustrating a step following the step in Fig. 7(r).

Fig. 8(t) is a sectional view illustrating a step following the step in Fig. 8(s).

Fig. 8(u) is a sectional view illustrating a step following the step in Fig. 8(t).

Fig. 9 is a plan view illustrating another configuration of cells according to the embodiment of the invention.

Fig. 10(l) is a sectional view illustrating another step of forming a cell according to the invention.

Fig. 10(m) is a sectional view illustrating a step following the step in Fig. 10(l).

Fig. 10(n) is a sectional view illustrating a step following the step in Fig. 10(m).

Fig. 11(o) is a sectional view illustrating a step following the step in Fig. 10(n).

Fig. 11(p) is a sectional view illustrating a step following the step in Fig. 11(o).

Fig. 11(q) is a sectional view illustrating a step following the step in Fig. 11(p).

Fig. 12(r) is a sectional view illustrating a step following the step in Fig. 11(q).

Fig. 12(s) is a sectional view illustrating a step following the step in Fig. 12(r).

Fig. 12(t) is a sectional view illustrating a step following the step in Fig. 12(s).

Fig. 13(u) is a sectional view illustrating a step following the step in Fig. 12(t).

Fig. 14(a) is a sectional view illustrating a substrate used to manufacture an IGBT according to the embodiment of the invention.

Fig. 14(b) is a sectional view illustrating a structure of a cell of the IGBT according to the embodiment of the

invention.

Fig. 15(a) is a sectional view illustrating a substrate used to manufacture another IGBT according to the embodiment of the invention.

Fig. 15(b) is a sectional view illustrating a step for manufacturing the IGBT according to the embodiment of the invention.

Fig. 15(c) is a sectional view illustrating a step following the step in Fig. 15(b).

Fig. 15(d) is a sectional view illustrating a step following the step in Fig. 15(c).

Fig. 16(a) is a sectional view illustrating a structure of a cell of the other IGBT according to the embodiment of the invention.

Fig. 16(b) is a sectional view illustrating a structure of a cell of a bidirectional conduction switch according to the embodiment of the invention.

Fig. 17(a) is a plan view illustrating a configuration of cells of a power MOSFET according to the related art.

Fig. 17(b) is a sectional view illustrating the power MOSFET according to the related art.

【Description of the items】

1 ... power MOSFET (transistor)

11 ... silicon substrate

12 ... drain layer

15 ... P-type body region

19 ... gate insulating film

27 ... source region

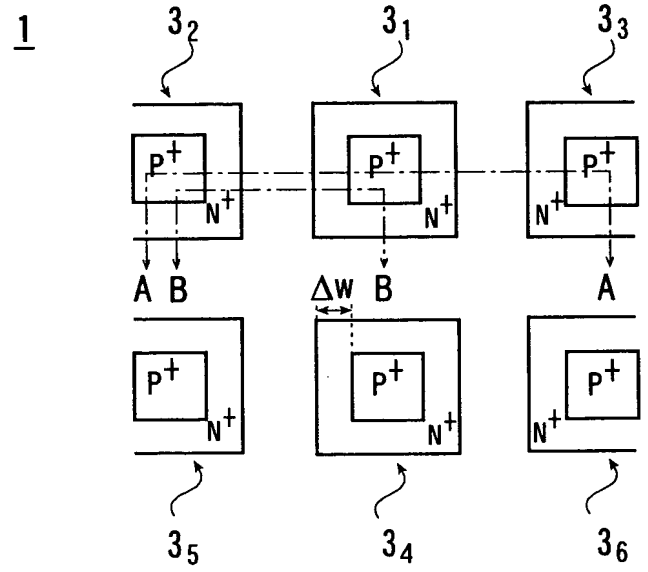
28 ... insulating film

30 ... polysilicon gate (gate electrode film)

[Title of document] Drawings

Fig. 1

(a)



(b)

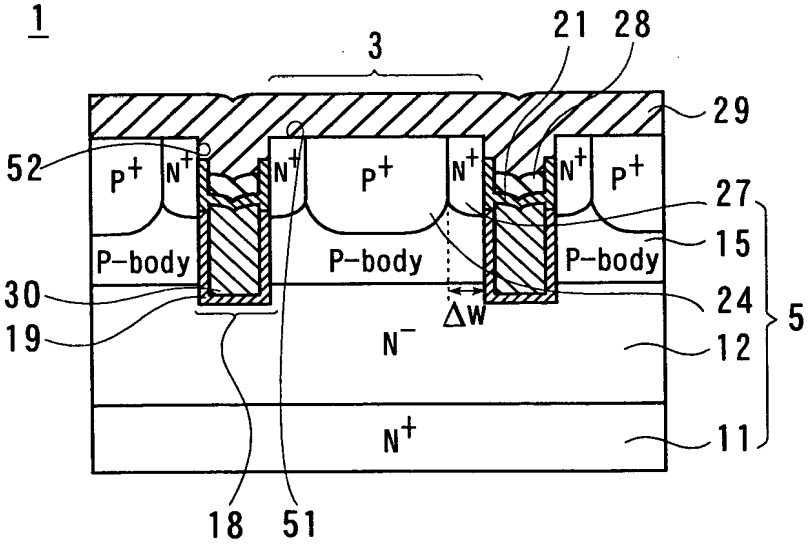
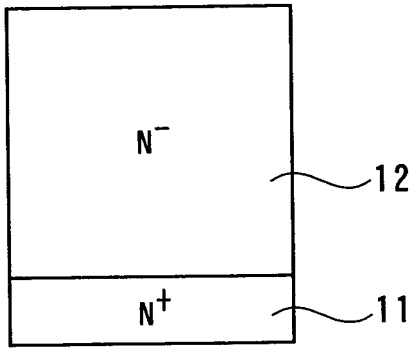
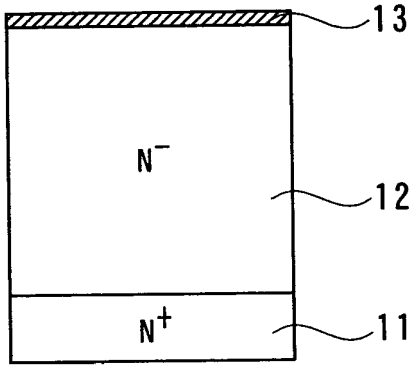


Fig.2

(a)



(b)



(c)

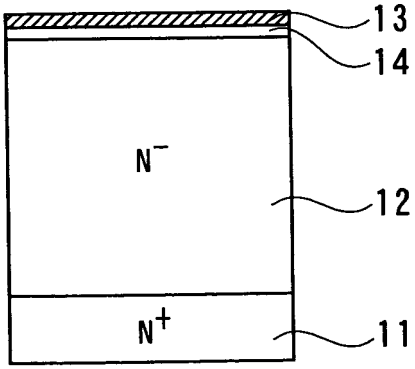
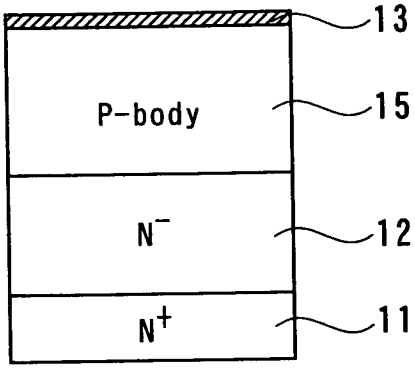
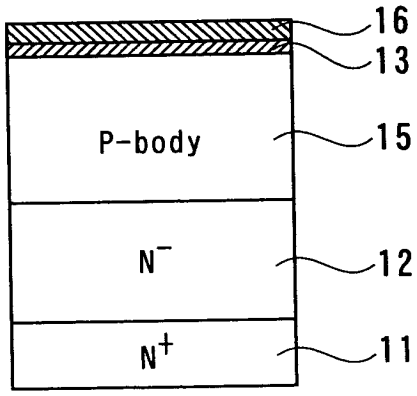


Fig. 3

(d)



(e)



(f)

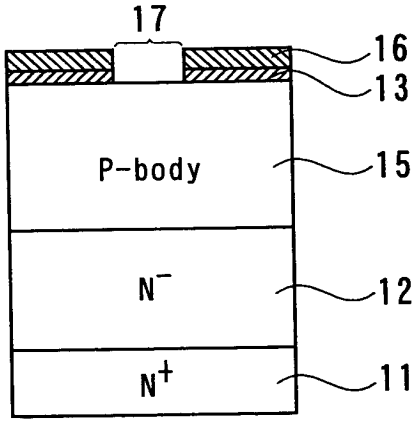
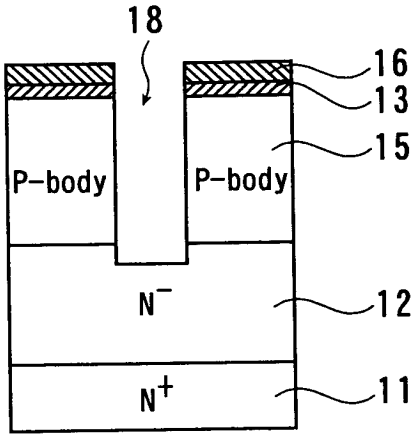
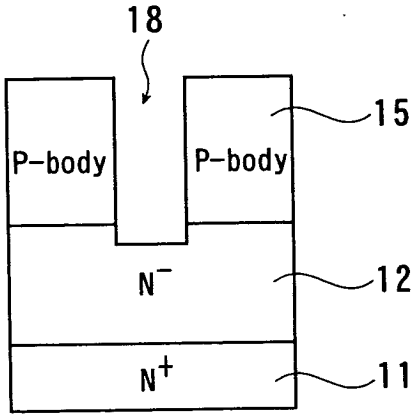


Fig. 4

(g)



(h)



(i)

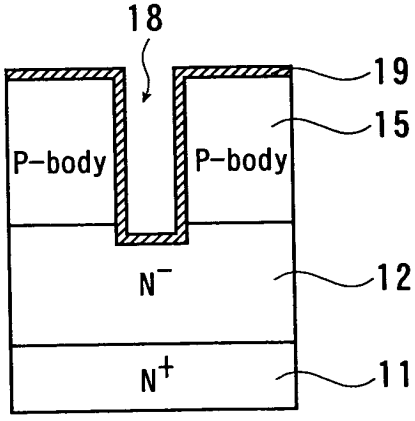
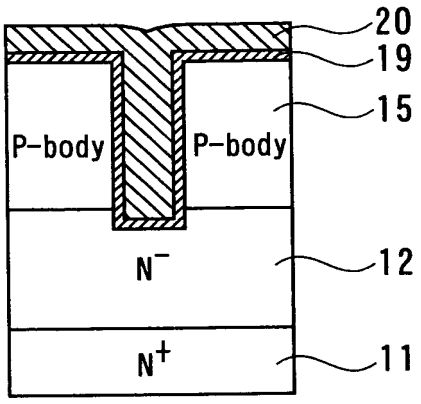
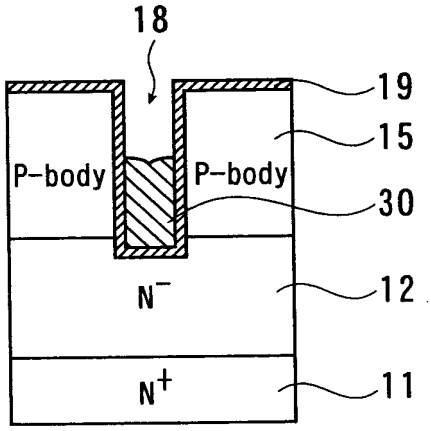


Fig. 5

(j)



(k)



(l)

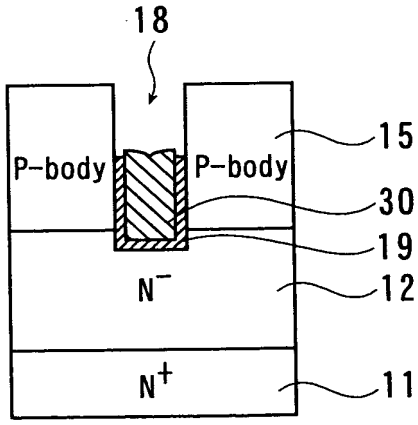
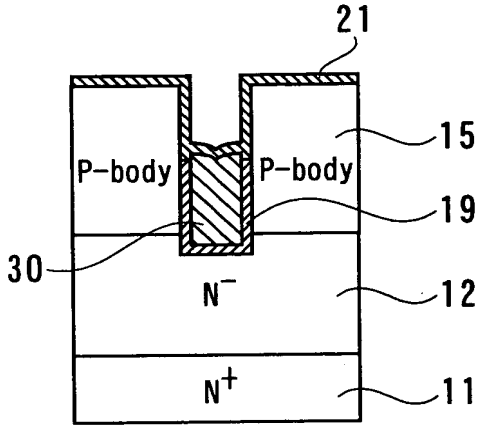
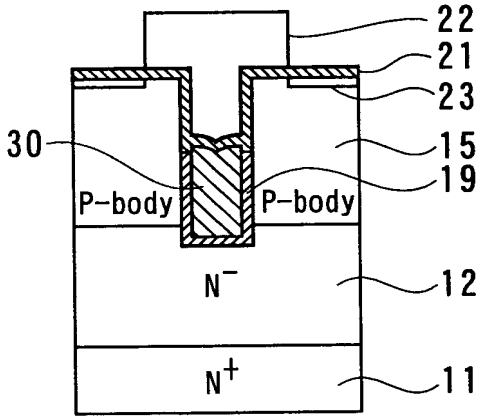


Fig.6

(m)



(n)



(o)

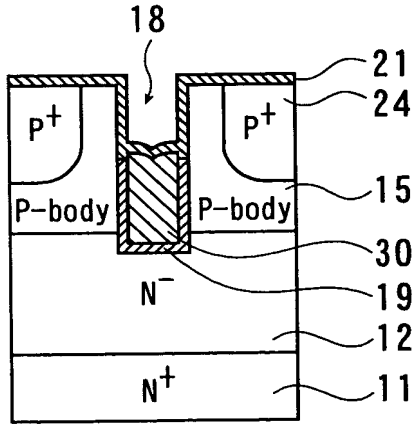
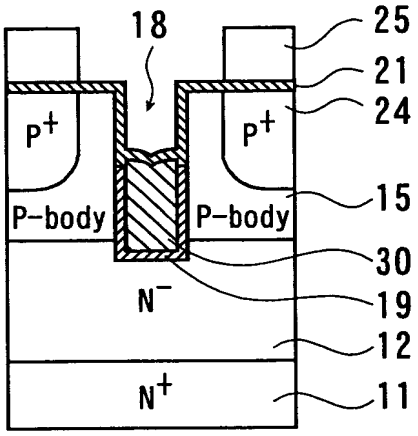
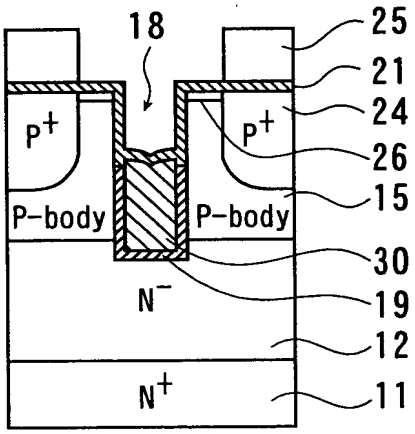


Fig. 7

(p)



(q)



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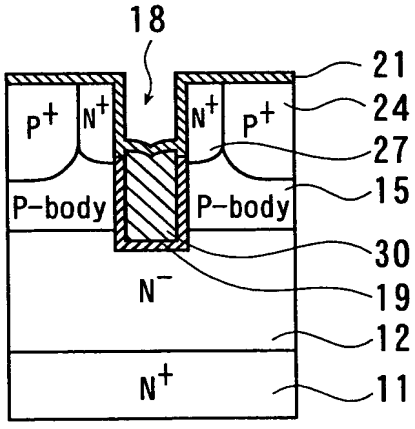
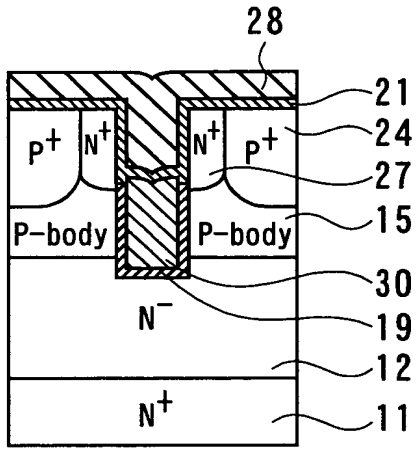


Fig. 8

(s)



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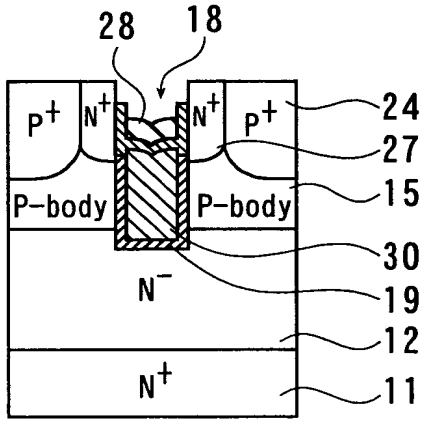


(u)

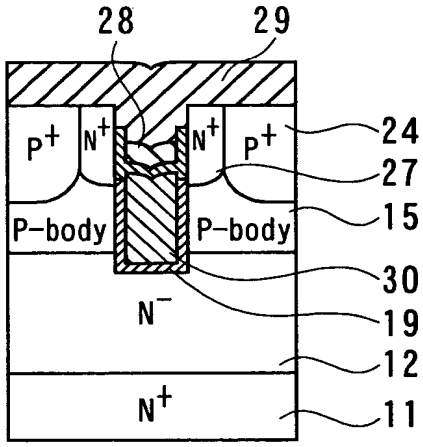


Fig. 9

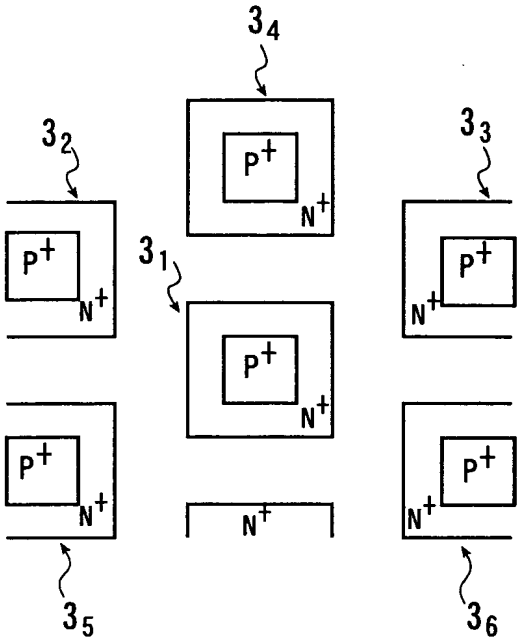
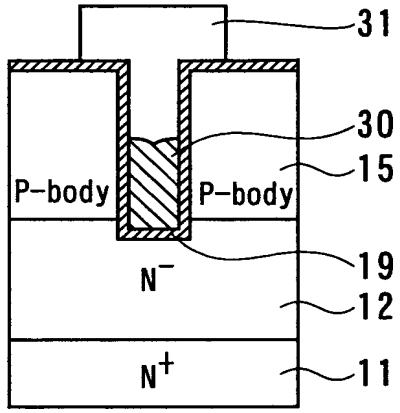
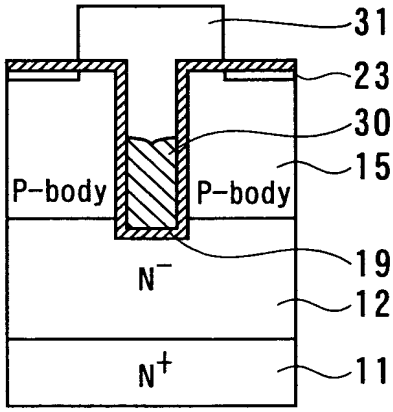


Fig. 10

(l)



(m)



(n)

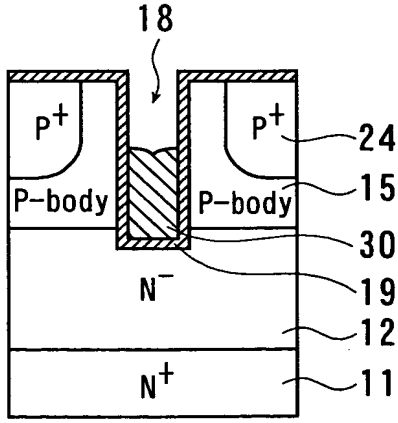
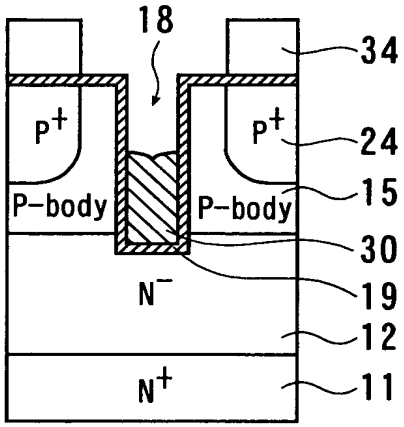
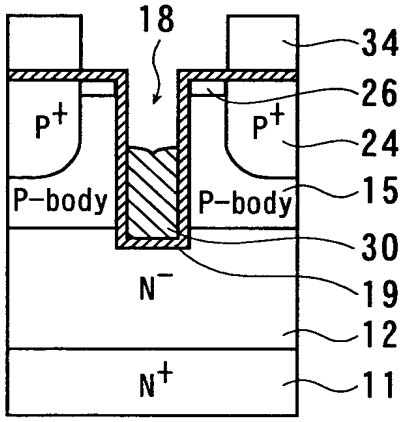


Fig. 11

(o)



(p)



(q)

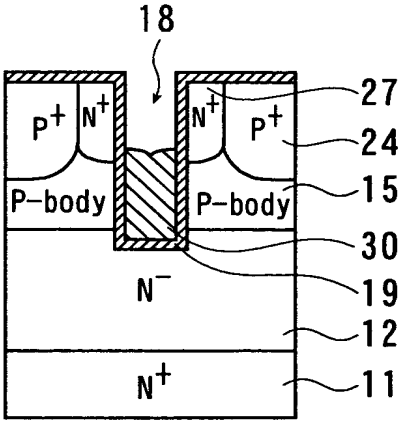
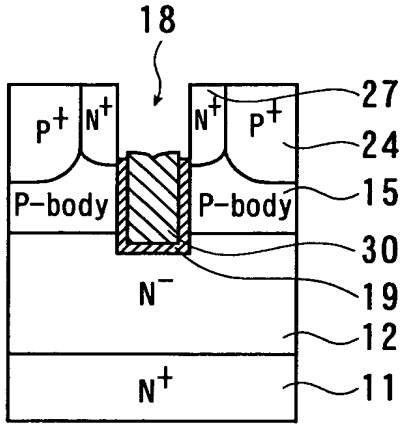
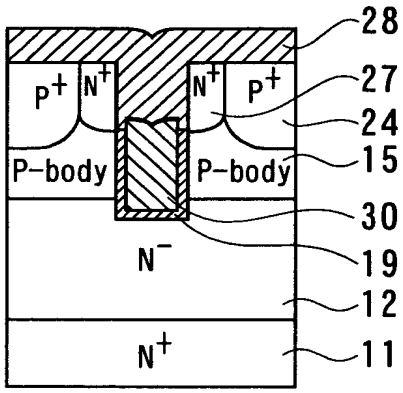


Fig. 12

(r)



(s)



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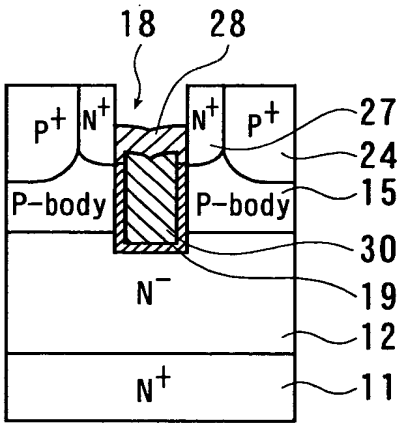


Fig. 13

(u)

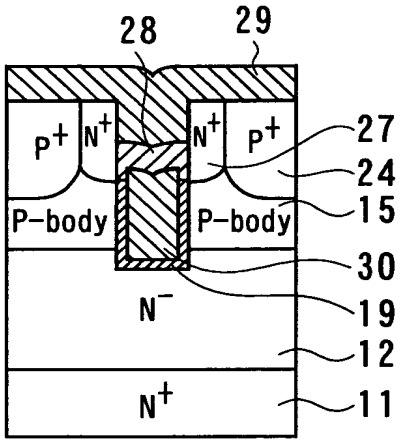
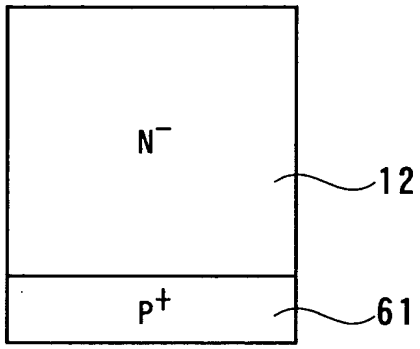


Fig. 14

(a)



(b)

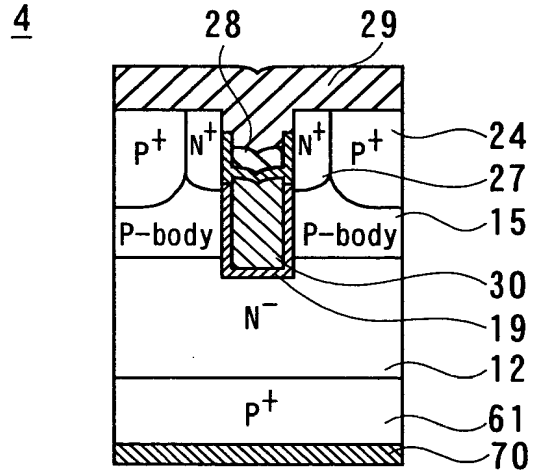
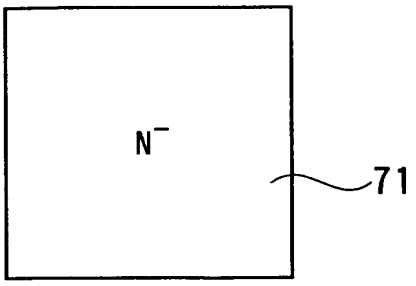


Fig. 15

(a)



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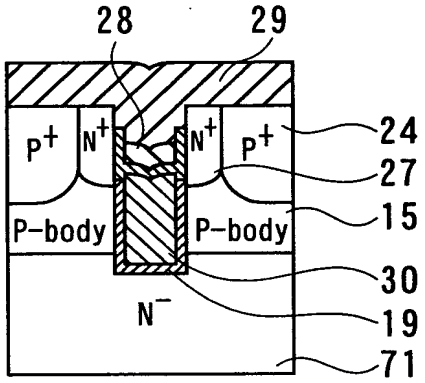

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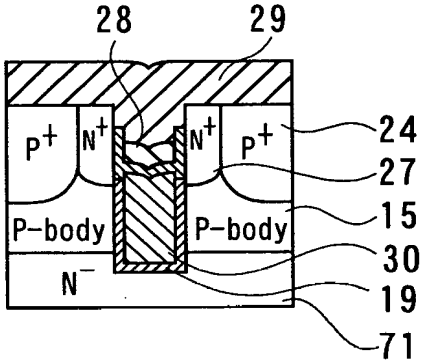

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(d)

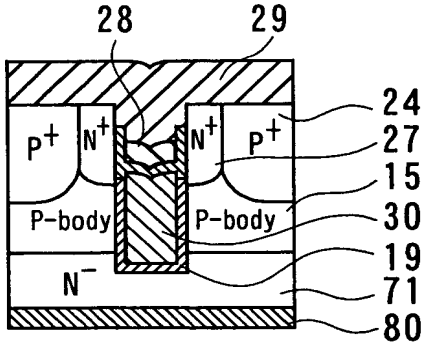
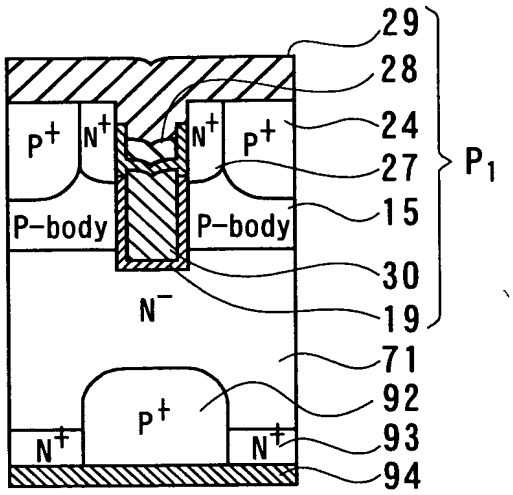


Fig. 16

(a)



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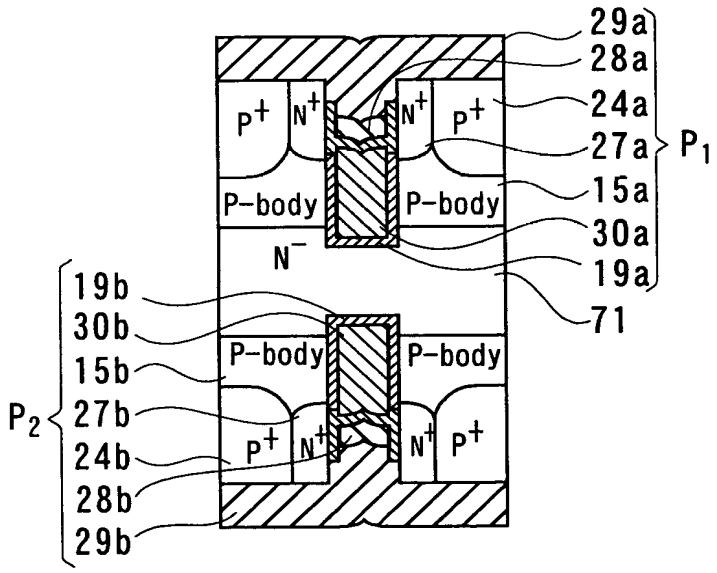
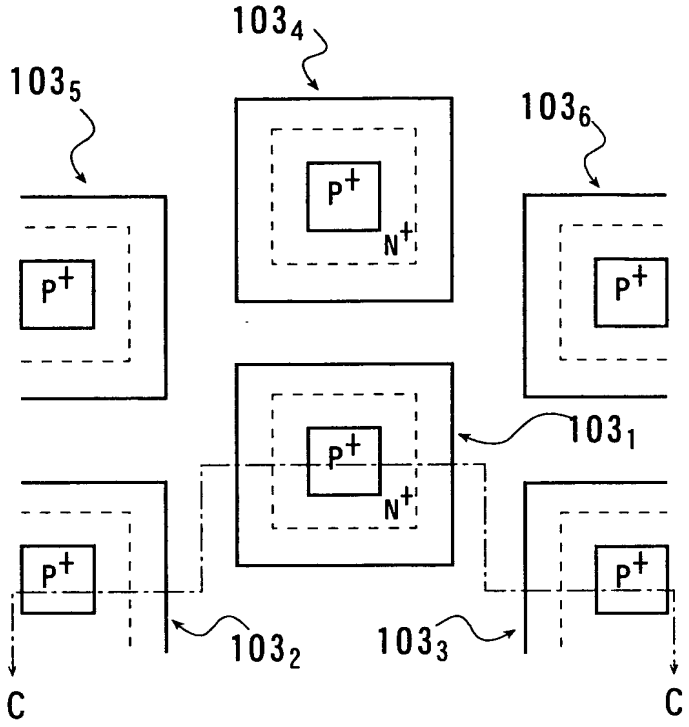


Fig. 17

(a)



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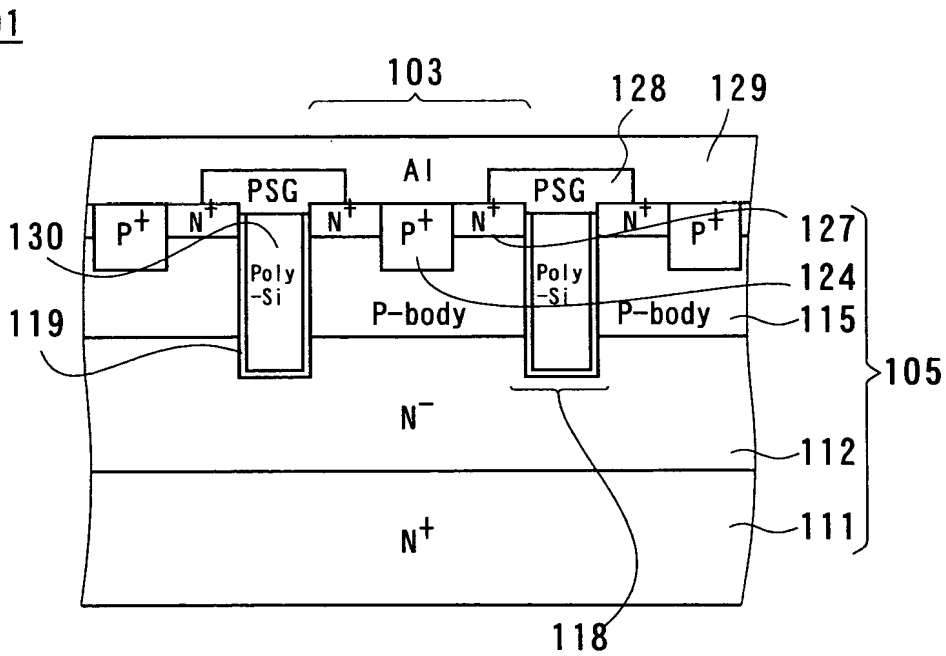

【DOCUMENT】 ABSTRACT

【Abstract】 ABSTRACT

【Subject】

A technique is provided which makes it possible to reduce the area of a power MOSFET.

A power MOSFET 1 according to the invention is a trench type in which a source region 27 is exposed on both of a substrate top surface 51 and an inner circumferential surface 52 of a trench 18. Since this makes it possible to provide contact between the source region 27 and a source electrode film 29 not only on the substrate top surface 51 but also on the inner circumferential surface 52 of the trench 18, source contact is provided with a sufficiently low resistance only on the substrate top surface, and the area of the device can be made smaller than that in the related art in which the source region 27 has been formed in a larger area.

【Most descriptive drawing for the invention】 Fig. 1

APPROVAL/ADDITIONAL INFORMATION

PATENT APPLICATION No. Hei 11-258687/1999

RECEIVED NO. 59900889138

TITLE OF DOCUMENT PATENT APPLICATION

AGENT HISAO URUMA 7277

DATE September 16, 1999

<APPROVAL INFORMATION/ADDITIONAL INFORMATION>

【APPLCANT(S)】

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HISTORY OF APPLICANT

REGISTRATION NUMBER [000002037]

1.CORRECTION DATE: AUGUST 28, 1990

[REASON FOR CORRECTION] NEW REGISTRATION

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NAME: SHINDENGEN ELECTRIC MANUFACTURING CO., LTD.